Giuseppe Luongo

List of Publications by Year
in descending order

29 papers	1,709 citations	361413 20 h-index	526287 27 g-index
29 all docs	29 docs citations	29 times ranked	2302 citing authors

#	Article	IF	Citations
1	Hysteresis in the transfer characteristics of MoS ₂ transistors. 2D Materials, 2018, 5, 015014.	4.4	209
2	Electrical transport and persistent photoconductivity in monolayer MoS₂phototransistors. Nanotechnology, 2017, 28, 214002.	2.6	189
3	Asymmetric Schottky Contacts in Bilayer MoS₂ Field Effect Transistors. Advanced Functional Materials, 2018, 28, 1800657.	14.9	162
4	Hybrid graphene/silicon Schottky photodiode with intrinsic gating effect. 2D Materials, 2017, 4, 025075.	4.4	127
5	Field Emission from Carbon Nanostructures. Applied Sciences (Switzerland), 2018, 8, 526.	2.5	125
6	Tunable Schottky barrier and high responsivity in graphene/Si-nanotip optoelectronic device. 2D Materials, 2017, 4, 015024.	4.4	122
7	A WSe₂ vertical field emission transistor. Nanoscale, 2019, 11, 1538-1548.	5.6	100
8	Gas dependent hysteresis in MoS ₂ field effect transistors. 2D Materials, 2019, 6, 045049.	4.4	79
9	Grapheneâ€“Silicon Schottky Diodes for Photodetection. IEEE Nanotechnology Magazine, 2018, 17, 1133-1137.	2.0	69
10	I-V and C-V Characterization of a High-Responsivity Graphene/Silicon Photodiode with Embedded MOS Capacitor. Nanomaterials, 2017, 7, 158.	4.1	63
11	Electronic properties of graphene/p-silicon Schottky junction. Journal Physics D: Applied Physics, 2018, 51, 255305.	2.8	63
12	Graphene enhanced field emission from InP nanocrystals. Nanotechnology, 2017, 28, 495705.	2.6	53
13	Effect of Electron Irradiation on the Transport and Field Emission Properties of Few-Layer MoS₂ Field-Effect Transistors. Journal of Physical Chemistry C, 2019, 123, 1454-1461.	3.1	51
14	Grapheneâ€“Silicon Device for Visible and Infrared Photodetection. ACS Applied Materials & Interfaces, 2021, 13, 47895-47903.	8.0	41
15	Field Emission Characterization of MoS2 Nanoflowers. Nanomaterials, 2019, 9, 717.	4.1	40
16	Field Emission from Self-Catalyzed GaAs Nanowires. Nanomaterials, 2017, 7, 275.	4.1	38
17	Transport and field emission properties of buckypapers obtained from aligned carbon nanotubes. Journal of Materials Science, 2017, 52, 6459-6468.	3.7	34
18	High field-emission current density from Î²-Ga2O3 nanopillars. Applied Physics Letters, 2019, 114, .	3.3	33

#	Article	IF	Citations
19	Bias Tunable Photocurrent in Metal-Insulator-Semiconductor Heterostructures with Photoresponse Enhanced by Carbon Nanotubes. Nanomaterials, 2019, 9, 1598.	4.1	29
20	Graphene Schottky Junction on Pillar Patterned Silicon Substrate. Nanomaterials, 2019, 9, 659.	4.1	22
21	Environmental effects on transport properties of PdSe2 field effect transistors. Materials Today: Proceedings, 2020, 20, 50-53.	1.8	15
22	Space charge limited current and photoconductive effect in few-layer MoS₂. Journal of Physics: Conference Series, 2019, 1226, 012013.	0.4	14
23	Effect of silicon doping on graphene/silicon Schottky photodiodes. Materials Today: Proceedings, 2020, 20, 82-86.	1.8	8
24	Persistent Photoconductivity, Hysteresis and Field Emission in MoS2 Back-Gate Field-Effect Transistors. , 2018, , .		5
25	The role of the substrate in Graphene/Silicon photodiodes. Journal of Physics: Conference Series, 2018, 956, 012019.	0.4	5
26	Two-dimensional effects in Fowler-Nordheim field emission from transition metal dichalcogenides. Journal of Physics: Conference Series, 2019, 1226, 012018.	0.4	5
27	Field emission from mono and two-dimensional nanostructures. Materials Today: Proceedings, 2020, 20, 64-68.	1.8	4
28	Current leakage mechanisms related to threading dislocations in Ge-rich SiGe heterostructures grown on Si(001). Applied Physics Letters, 2021, 119, .	3.3	3
29	Invited talk â€" Graphene/silicon schottky diodes for photodetection. , 2017, , .		1